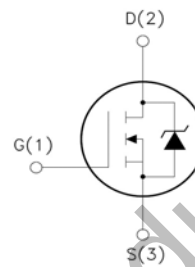
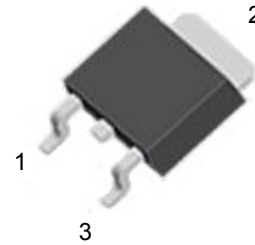


FQD2N65SE**Features:**

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 90nC (Typ.).
- ☐ BVDSS=650V,I_D=2A
- ☐ R_{DS(on)} : 4.8Ω (Max) @V_G=10V
- ☐ 100% Avalanche Tested

TO-252



- 1.Gate (G)
- 2.Drain (D)
- 3.Source (S)

Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{DSS}	Drain-Source Voltage		650	V
I _D	Drain Current	T _C =25°C	2	A
		T _C =100°C	1.5	
V _{GSS}	Gate-Source Voltage		±30	V
E _{AS}	Single Pulse Avalanche Energy (note1)		120	mJ
I _{AR}	Avalanche Current (note2)		2	A
P _D	Power Dissipation (Ta=25°C)		40	W
T _j	Junction Temperature(Max)		150	°C
T _{stg}	Storage Temperature		-55~+150	
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		300	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance, Junction to Case	-	2.87	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	-	50	

Electrical Characteristics (Ta=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0	650	-	-	V
ΔBVDSS/ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA ,Reference to 25℃	-	0.4	-	V/℃
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650V, V _{GS} =0V V _{DS} =520V, T _C =125℃	-	-	1 10	μA
I _{GSSF}	Gate-body leakage Current, Forward	V _{GS} =+30V, V _{DS} =0V	-	-	100	nA
I _{GSSR}	Gate-body leakage Current, Reverse	V _{GS} =-30V, V _{DS} =0V	-	-	-100	
On Characteristics						
V _{GS(TH)}	Gate Threshold Voltage	I _D =250μA, V _{DS} =V _{GS}	2	-	4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	I _D =1A, V _{GS} =10V	-	4.5	4.8	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0, f=1.0MHz	-	270	350	pF
C _{oss}	Output Capacitance		-	40	50	
C _{rss}	Reverse Transfer Capacitance		-	5	7	
Switching Characteristics						
T _{d(on)}	Turn-On Delay Time	V _{DD} =325V, I _D =2A R _G =25Ω (Note 3,4)	-	10	30	ns
T _r	Turn-On Rise Time		-	25	60	
T _{d(off)}	Turn-Off Delay Time		-	20	50	
T _f	Turn-Off Rise Time		-	25	60	
Q _g	Total Gate Charge	V _{DS} =520V, V _{GS} =10V, I _D =2A (Note 3,4)	-	90	110	nC
Q _{gs}	Gate-Source Charge		-	1.6	-	
Q _{gd}	Gate-Drain Charge		-	4.3	-	
Drain-Source Diode Characteristics and Maximum Ratings						
I _s	Max. Diode Forward Current	-	-	-	2	A
I _{SM}	Max. Pulsed Forward Current	-	-	-	8	
V _{SD}	Diode Forward Voltage	I _D =2A	-	-	1.5	V
T _{rr}	Reverse Recovery Time	I _S =2A, V _{GS} =0V diF/dt=100A/μs	-	180	-	ns
Q _{rr}	Reverse Recovery Charge	(Note3)	-	0.72	-	μC

Notes : 1, L=60mH, IAS=2A, VDD=50V, RG=25Ω, Starting TJ =25°C

2, Repetitive Rating : Pulse width limited by maximum junction temperature

3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

4, Essentially Independent of Operating Temperature

Typical Characteristics

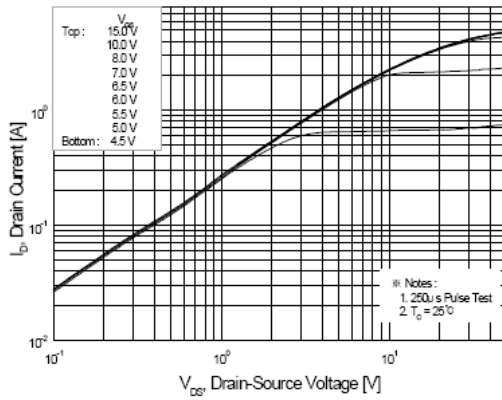


Figure 1. On-Region Characteristics

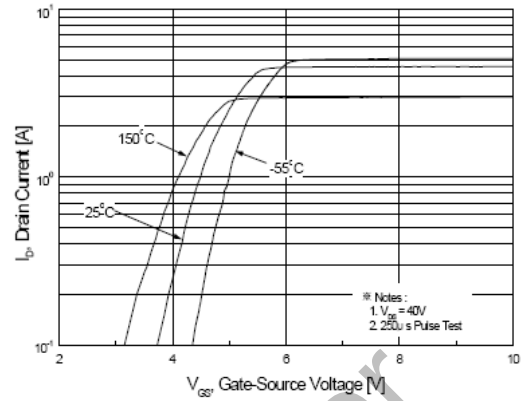


Figure 2. Transfer Characteristics

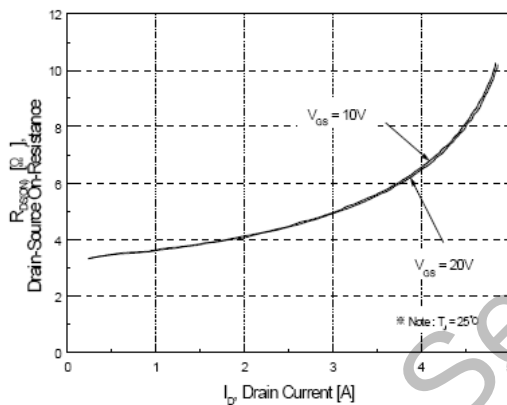


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

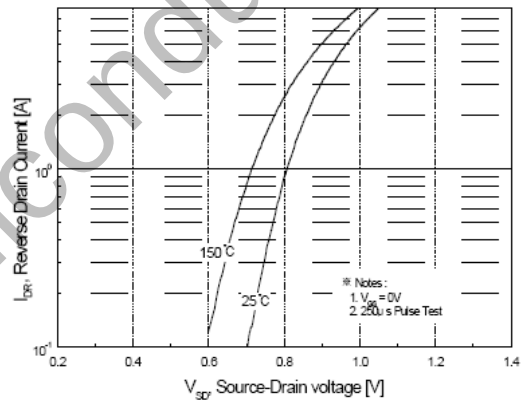


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

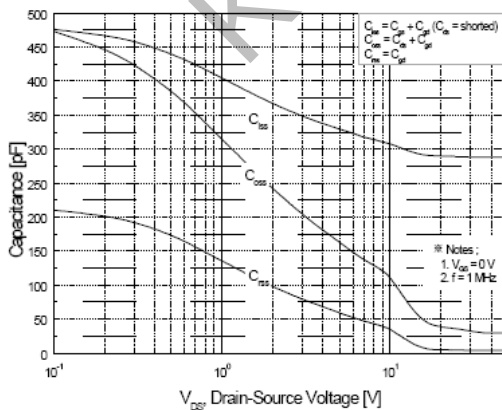


Figure 5. Capacitance Characteristics

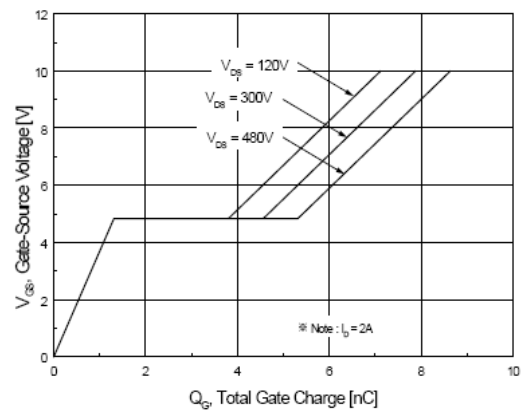


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

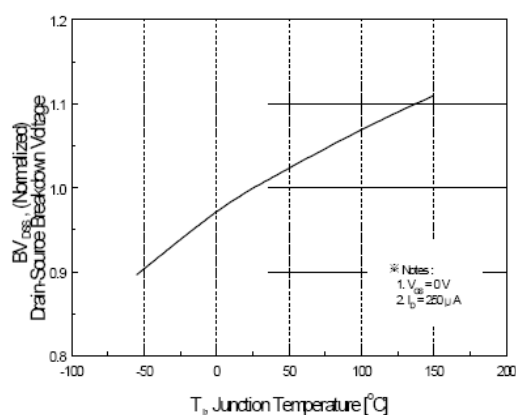


Figure 7. Breakdown Voltage Variation vs Temperature

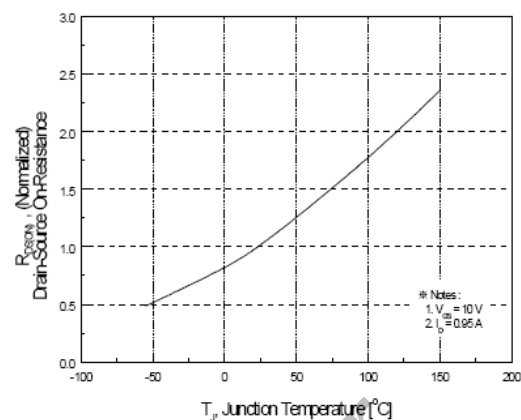


Figure 8. On-Resistance Variation vs Temperature

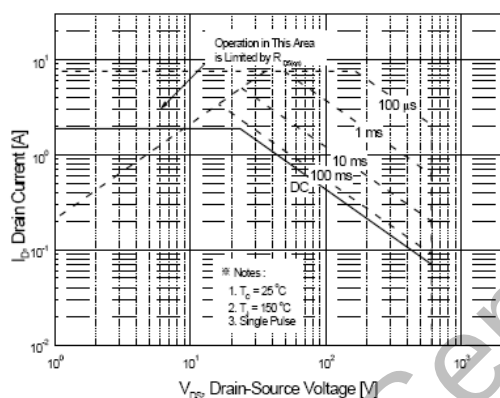


Figure 9. Maximum Safe Operating Area

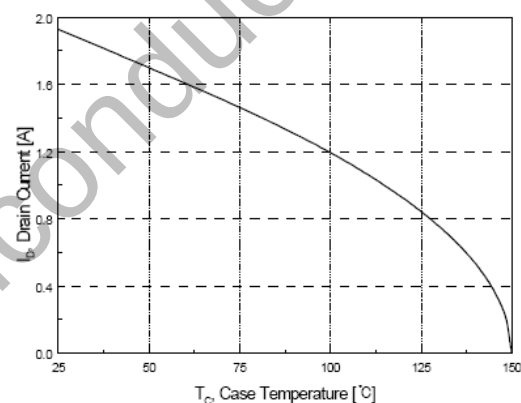


Figure 10. Maximum Drain Current vs Case Temperature

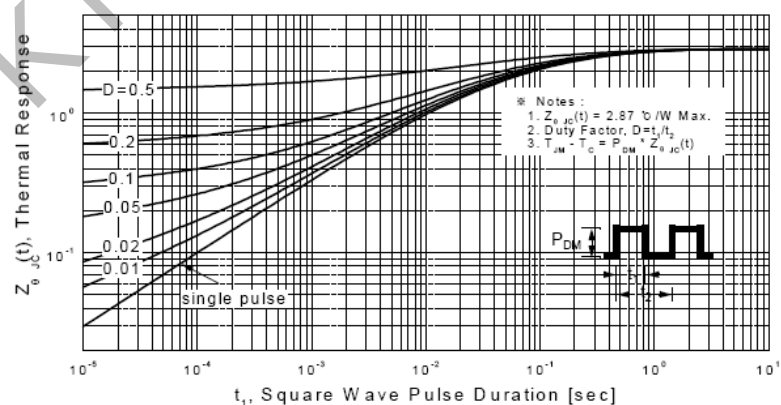
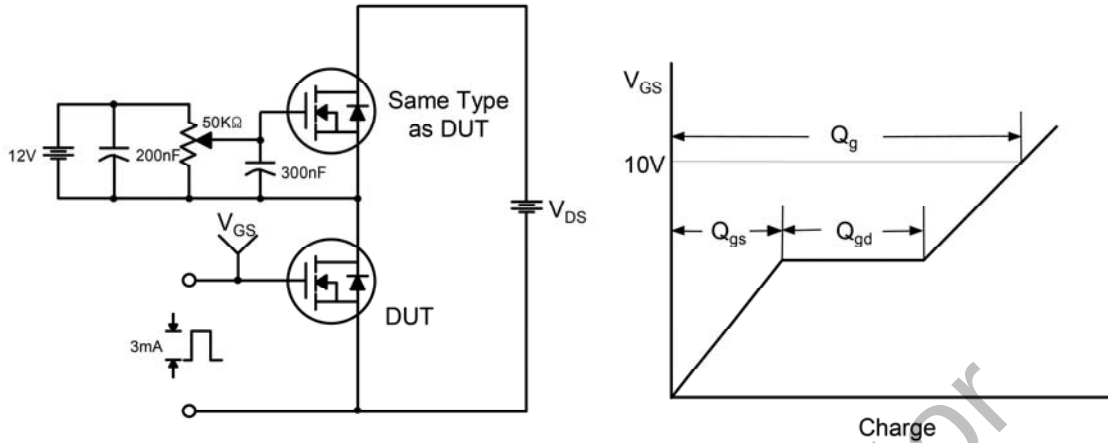
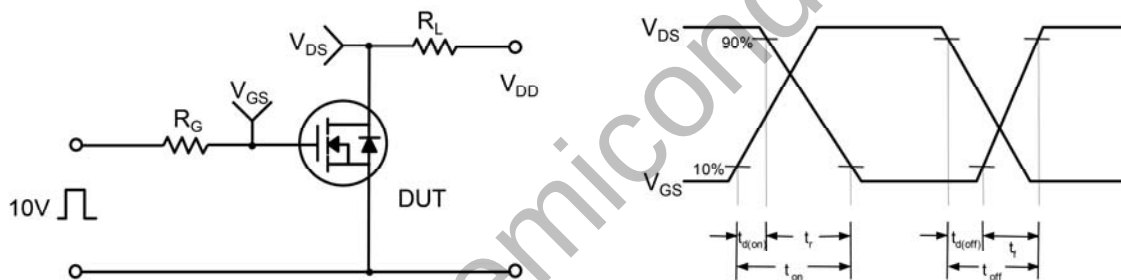


Figure 11. Transient Thermal Response Curve

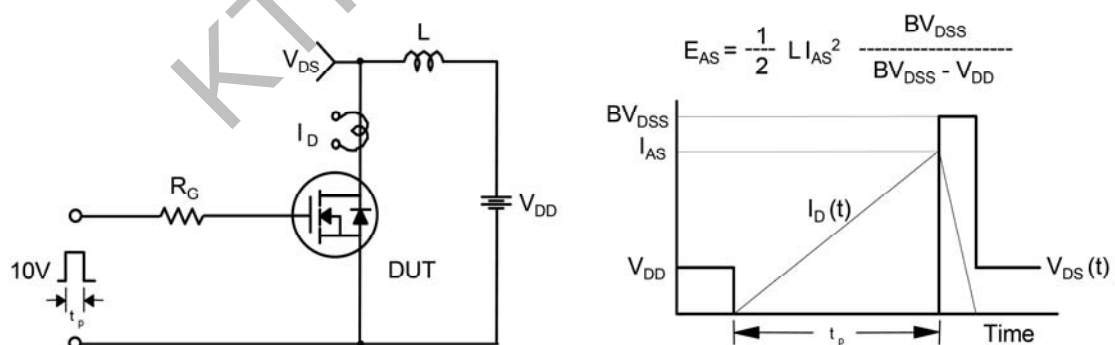
Gate Charge Test Circuit & Waveform



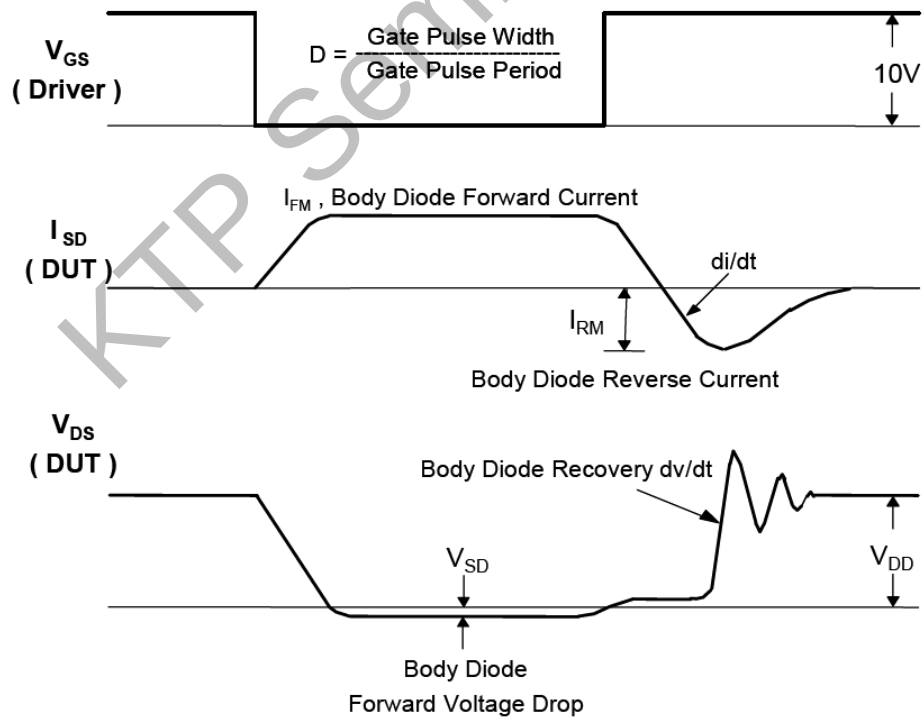
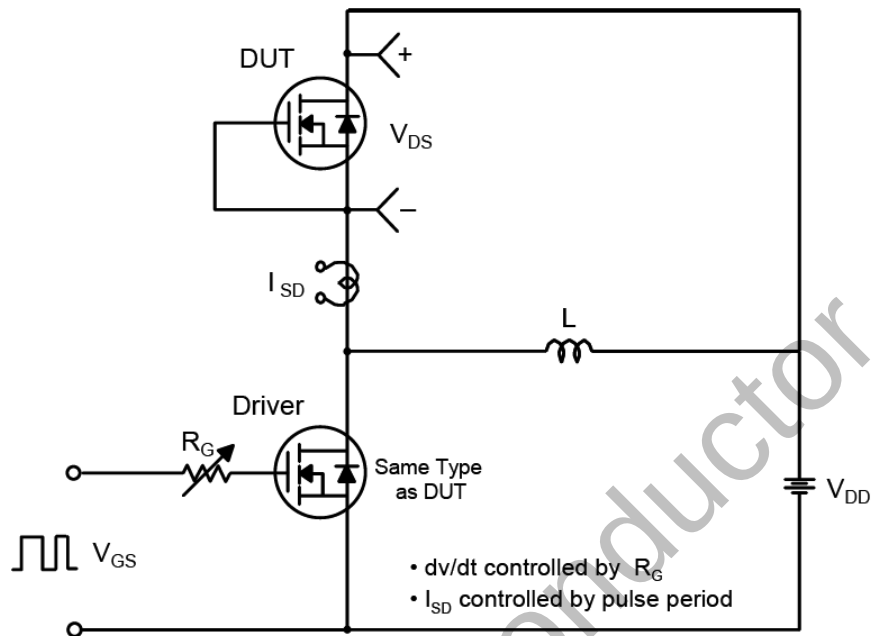
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveform



Package Dimension

TO-252

Unit: mm

